

FIG.1

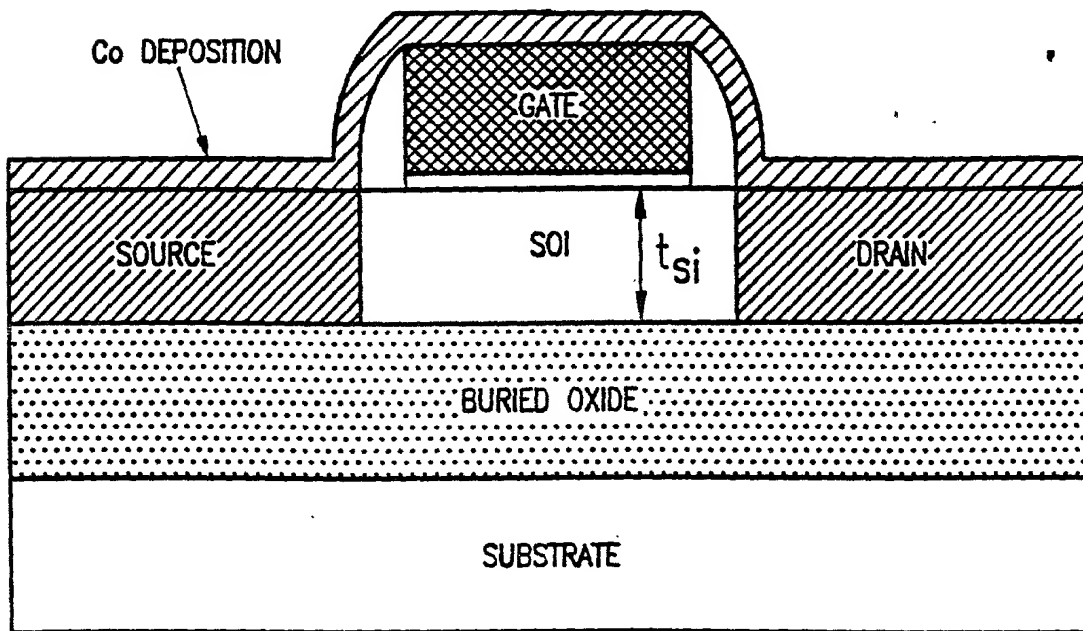


FIG.2

09902483-071101

FORM  $\text{Co}_2\text{Si}$  BY LOW TEMPERATURE ANNEAL

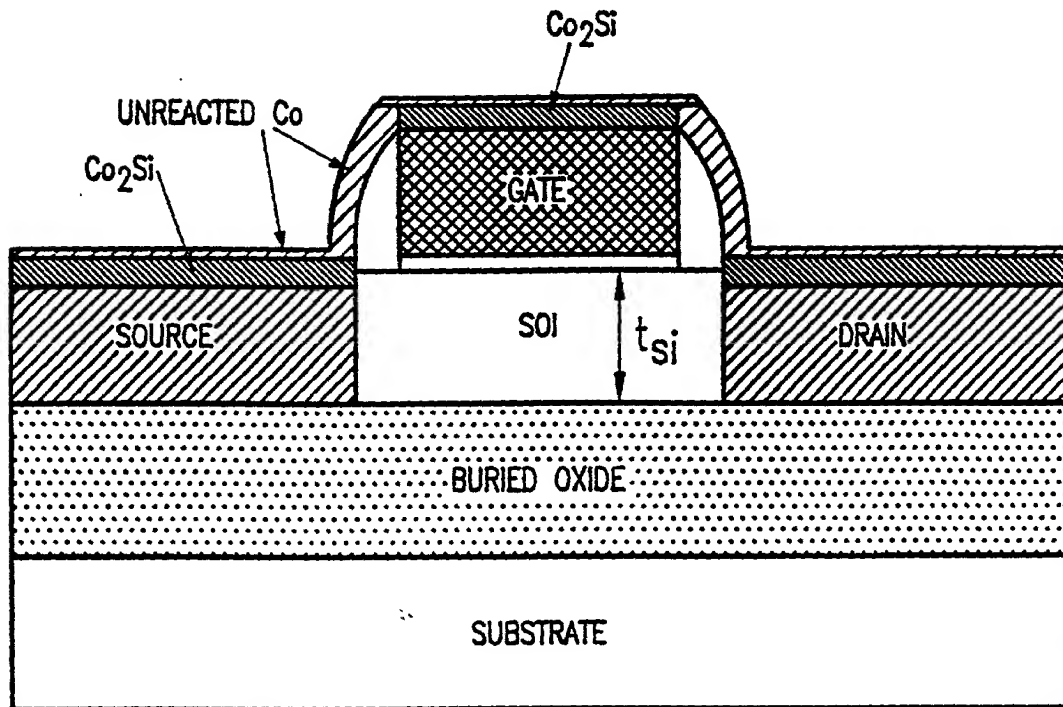


FIG.3

DEPOSITE  $\alpha\text{-Si}$

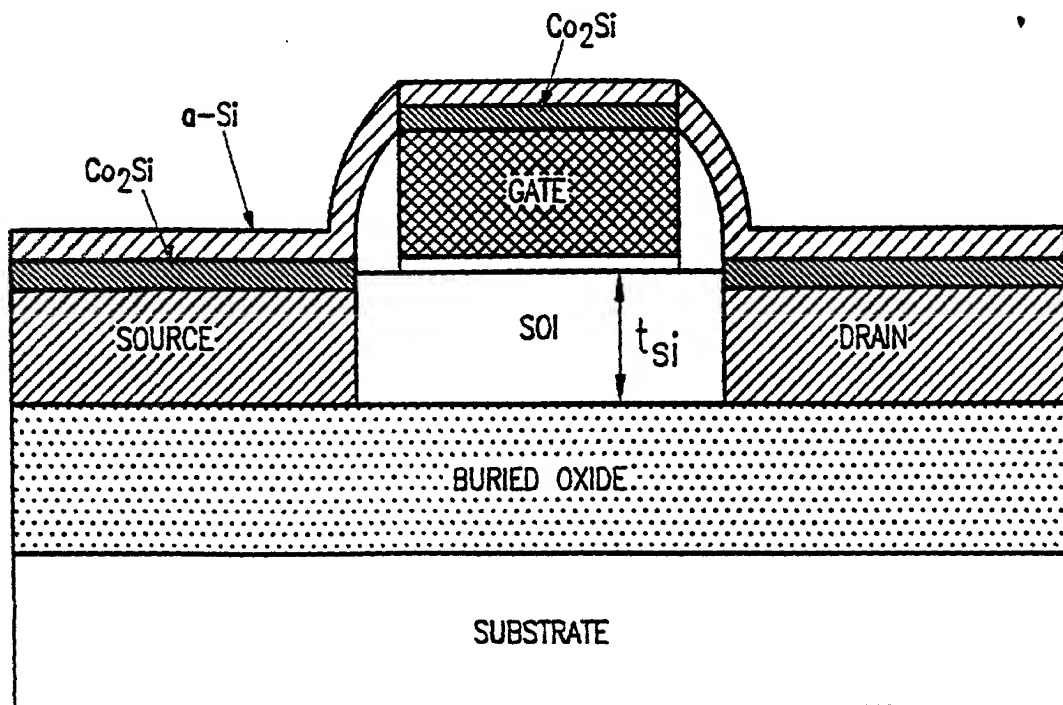


FIG.4

FIG. 3

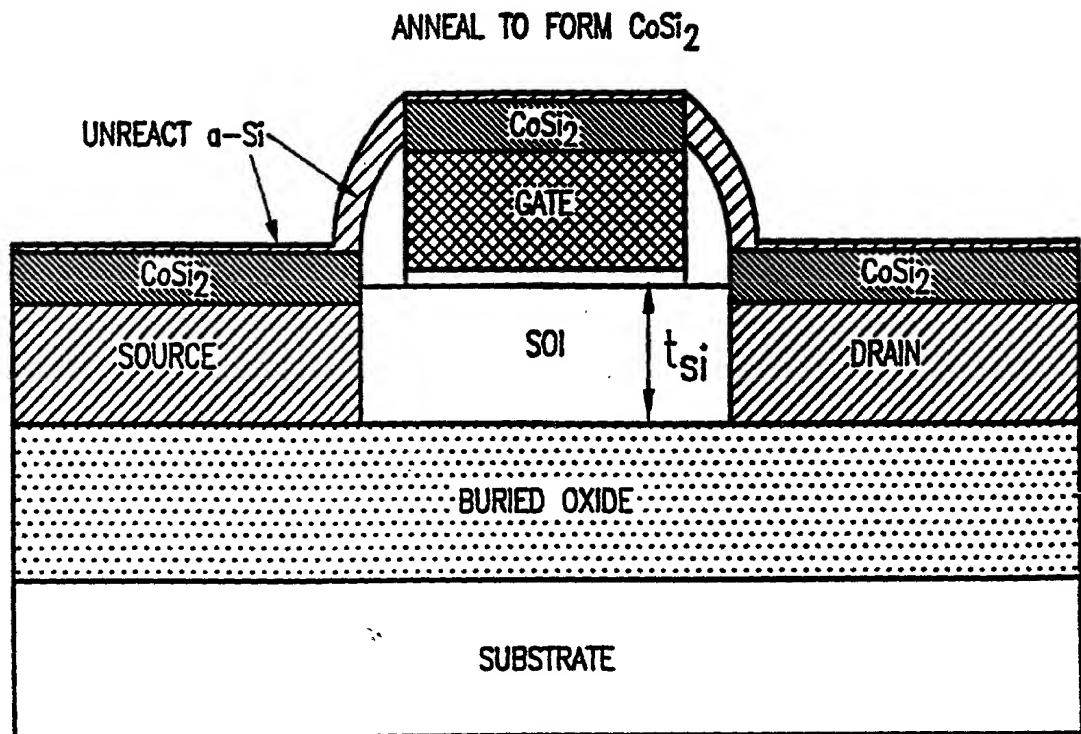


FIG.5

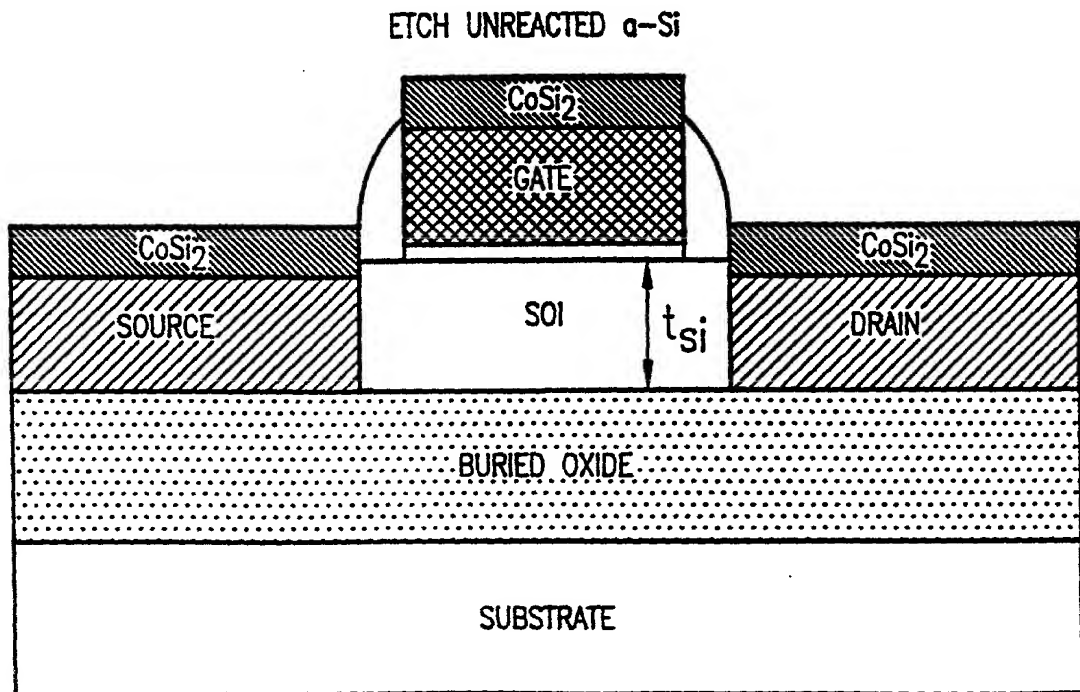
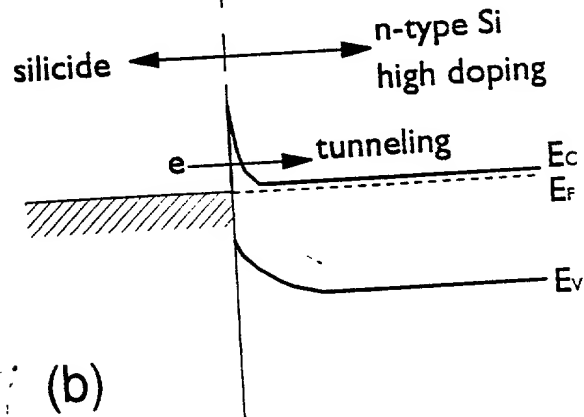
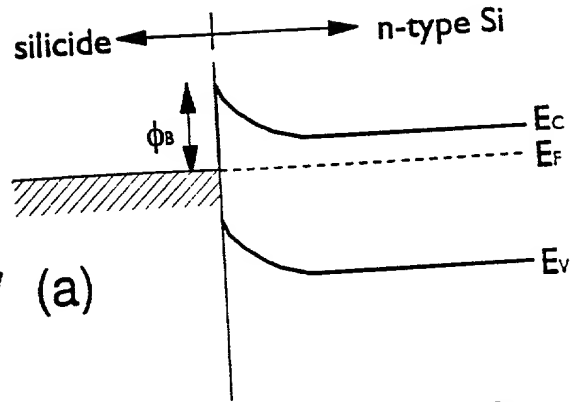


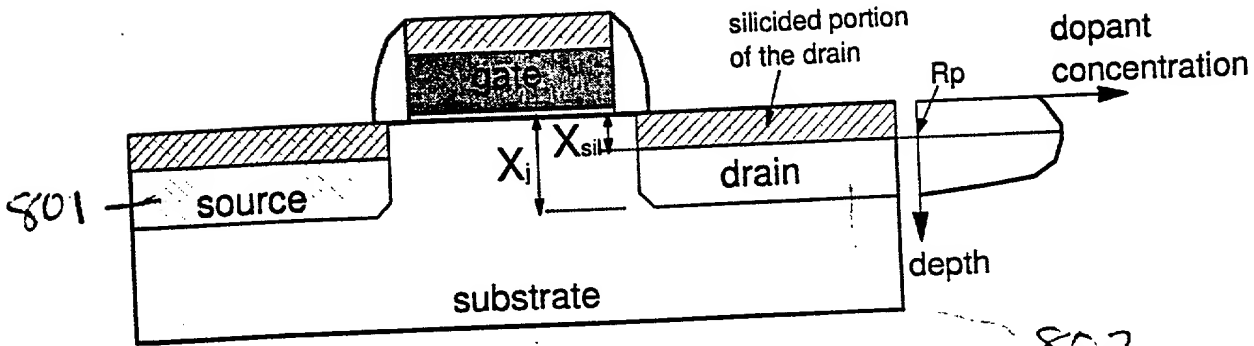
FIG.6

FIG. 5



09902493-074404  
TOP SECRET

800



$X_j$  = source or drain junction depth  
 $X_{sil}$  = silicide junction depth  
 $R_p$  = peak dopant concentration

Requirements:

1.  $X_j > X_{sil}$
2.  $X_{sil}$  roughly equals  $R_p$

Figure 8

0590483-071104 TOT 20" EST 20650

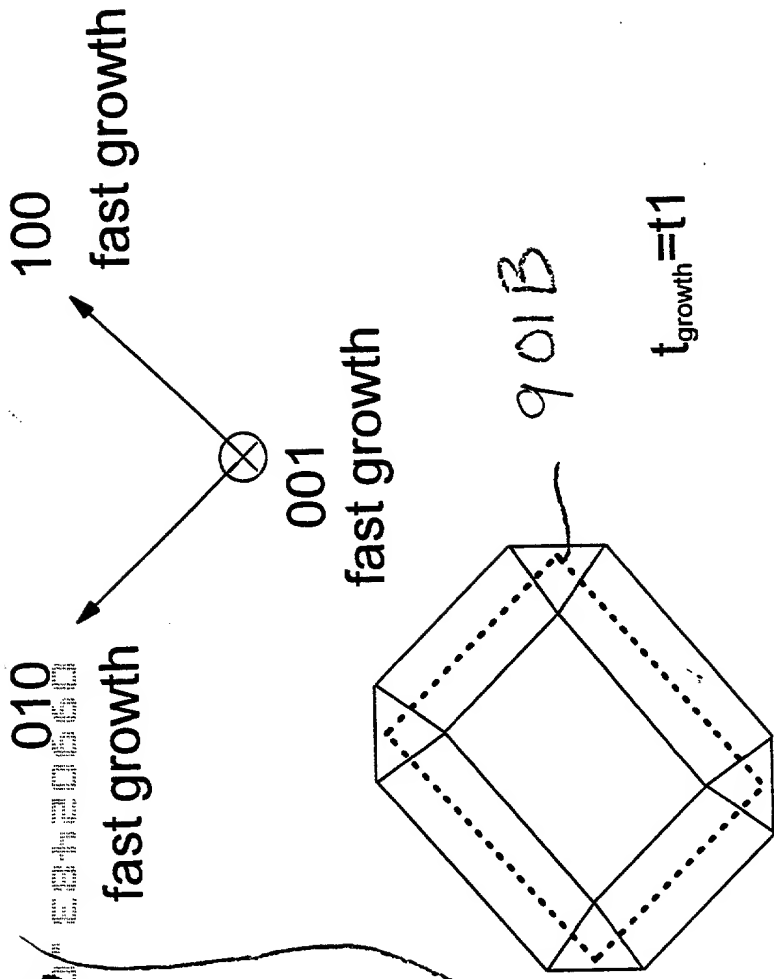
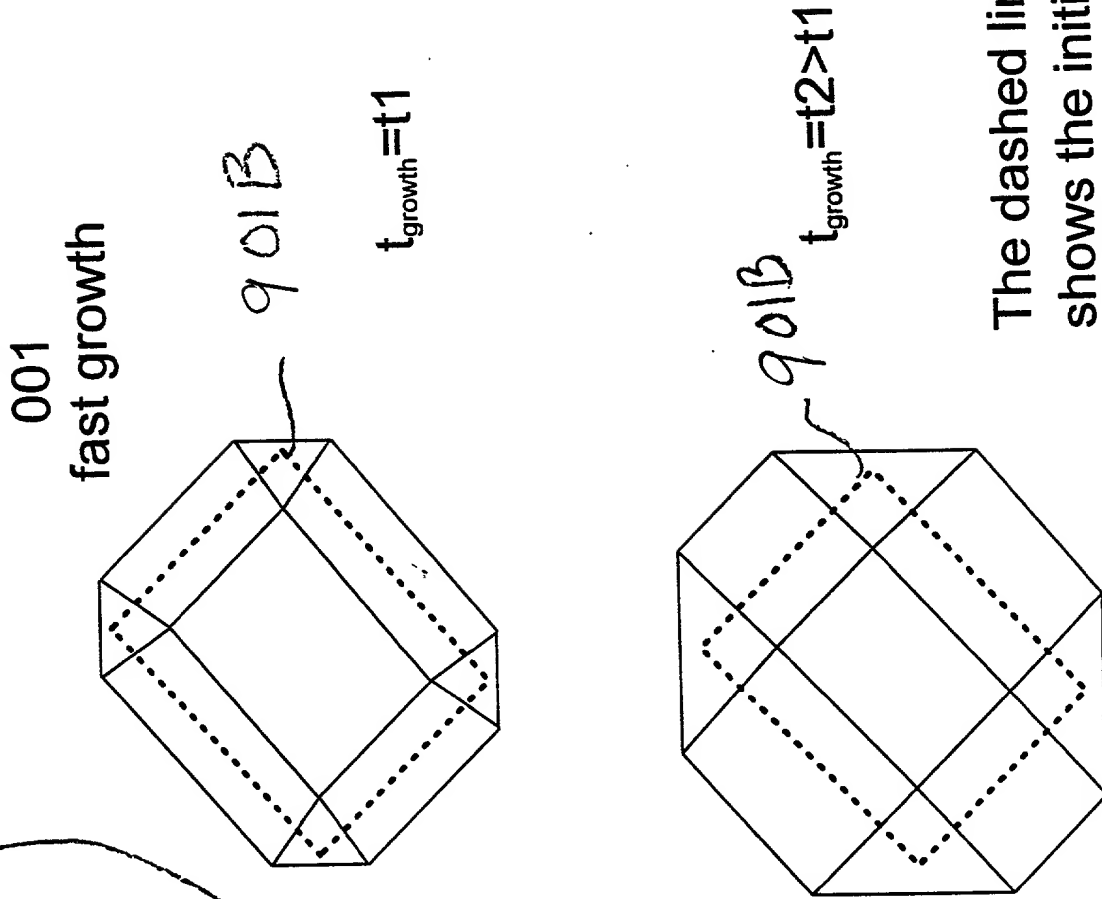


Fig. 9B



The dashed line shows the initial growth window which is defined by the hard mask